# Implementation of phonon dispersion with LO-TO splitting for polar materials

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## Phonon

<u>Phonons are vibrations of the atoms in a crystal lattice, and have resonant</u> <u>frequencies in the infrared spectral region.</u> The atoms in a solid are bound to their equilibrium positions by the forces that hold the crystal together. When atoms are displaced from their equilibrium positions, they experience restoring forces, and vibrate at characteristic frequencies. The relationship between frequencies and **k** is called phonon dispersion.

M. Fox, "Optical Properties of Soilds", 2nd. Chapter 10.

Phonon's dispersion relation can be obtained directly using the quantum-mechanical approach.



Phys. Rev. Lett. 48 (1982) 1846.

### Methods of calculting phonon dispersion

There are three methods to calculate phonon dispersion of solids in the First principle calculation - direct approach, linear response approach, and molecular dynamic approach.

Table 1. The linear-response approach versus the direct approach					
Features	Linear response approach	Direct approach			
Implementation in DFT	Calculate the dynamical matrix in the reciprocal space	Calculate the interatomic interaction force constants in the real space			
Advantage	Dynamical matrix can be accurately calculated at any arbitrary <b>q</b> (wave-vector) points	Straightforward to determine the total energy as a function of atomic displacements			
Disadvantage	Extensive programming required and it sometimes has special requirements for the form of pseudopotential in DFT calculations	Phonon frequencies can be accurately calculated only at <b>q</b> points that are commensurate with supercell geometry			
Limitation on ${f k}$ point mesh	<b>k</b> point meshes for electronic structure and phonon calculations should be compatible	No need			
Additional calculations for polar materials	Separate calculation of dynamical matrix at $\Gamma$ point, Born effective charges and dielectric constants; additional calculation to separate coulombic contribution from dynamical matrix	Separate calculation of Born effective charges and dielectric constants			
For accurate phonon dispersions or density of states for polar solids	Forward Fourier interpolation using the interatomic force constants followed by adding the coulombic contribution back.	Adding coulombic contribution as a constant term to the interatomic force constants followed by forward Fourier interpolation			

### Phonon / First-principles codes for calculting phonon dispersion

Table 2.         A collection of phonon/first-principles codes					
Codes	Abilities	Method to compute polar effects on phonons			
PWSCF/QUANTUM ESPRESSO <sup>14</sup>	Electronic structure; phonon	Linear-response approach			
ABINIT	Electronic structure; phonon	Linear-response approach			
CASTEP <sup>13</sup>	Electronic structure; phonon	Linear-response approach			
CRYSTAL <sup>28</sup>	Electronic structure; phonon	Mixed-space approach			
VASP <sup>11,12</sup>	Electronic structure; phonon	Not available			
YPHON <sup>23</sup>	Phonon	Mixed-space approach			
ShengBTE <sup>8</sup>	Phonon; thermal conductivity; thermodynamic properties	Mixed-space approach			
PhonTS <sup>7</sup>	Phonon; thermal conductivity; thermodynamic properties	Mixed-space approach			
Phonopy <sup>18</sup>	Phonon; thermal conductivity; thermodynamic properties	Mixed-space approach			
ALAMODE <sup>24</sup>	Phonon; thermal conductivity; thermodynamic properties; anharmonicity	Mixed-space approach			
PHONON17,25-27	Phonon; thermodynamic properties	Only accurate at the $\Gamma$ point			
PHON <sup>21</sup>	Phonon; thermodynamic properties	Not available			
ATAT <sup>4,22</sup>	Phonon; thermodynamic properties	Not available			

Y. Wang et. al, Comptational Material 2, 16006 (2016).

### **3D crystal system**

Interatomic Force constants (IFCs)

$$u_{n-1} \qquad u_n \qquad u_{n+1} \qquad \text{direction } \alpha$$

$$\underbrace{\bullet}_{I\alpha J\beta} \uparrow \underbrace{\bullet}_{a}$$

$$\underbrace{\bullet}_{a \text{tom } J} \qquad \underbrace{\bullet}_{a \text{tom } J}$$

$$K_{I\alpha J\beta}(R - R') = \frac{\partial^2 E_{tot}}{\partial u_{I\alpha}(R) \partial u_{J\beta}(R')} = -\frac{\partial F_{I\alpha}}{\partial u_{J\beta}(R')}$$
(1)

The displacement of I-th atom along the direction  $\alpha$  in Bravais lattice R

Dynamical matrix

$$\widetilde{D}_{I\alpha J\beta}(\vec{q}) = \frac{1}{\sqrt{m_I m_J}} \sum_{\vec{R}, \vec{R}'} K_{I\alpha J\beta} \left(\vec{R}' - \vec{R}\right) e^{i\vec{q} \cdot (\vec{R}' - \vec{R})}$$
(2)  
Mass of I-th atom

$$\omega^2(\vec{q})\vec{U}_{I\alpha}(\vec{q}) = \widetilde{D}_{I\alpha J\beta}(\vec{q})\vec{U}_{J\beta}(\vec{q})$$
(3)

http://www.openmx-square.org/workshop/meeting15/index.html

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# Force constant $K_{I\alpha,J\beta}(R-R') = \frac{\partial^2 E_{tot}}{\partial \mu_{I\alpha}(R) \partial \mu_{J\beta}(R')} = -\frac{\partial F_{I\alpha}}{\partial \mu_{J\beta}(R')}$ (1)Center difference approximation $\frac{f(x+\Delta x)-f(x-\Delta x)}{2\Delta x}$ f'(x) =(31)Displacement

Atomic coordinate x at equilibrium state

### Acoustic sum rules

#### 2. Sum rules in the matrix of force constants

We will be concerned with satisfying two properties of the matrix of force constants [8],  $\Phi_{i\alpha,j\beta}$  (where *i* and *j* label the atoms and  $\alpha$  and  $\beta$  label Cartesian directions) which are difficult to impose simultaneously in *ab initio* lattice dynamics. Firstly, it should be symmetric because partial differentiation is commutative:

$$\Phi_{i\alpha,j\beta} = \Phi_{j\beta,i\alpha} \tag{2}$$

although from equation (1) we see that this explicit symmetry is missing when the element is calculated from the force. Secondly, it should obey the following sum rule which follows from Newton's third law:

$$\Phi_{i\alpha,i\beta} = -\sum_{j\neq i} \Phi_{i\alpha,j\beta}.$$
(3)

It follows from these two rules that:

$$\sum_{j \neq i} \Phi_{i\alpha, j\beta} = \sum_{j \neq i} \Phi_{i\beta, j\alpha}.$$
 (4)

These three rules are true regardless of the actual symmetry of the system under consideration. If the force calculation is exact, then the rules above are automatically satisfied.

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Flow chart of phonon dispersion

### For example: Graphene

- 1. Setup input file and keywords.
- 2. Displace atoms along x/y/z directions, i.e. x, -x, y, -y, z, -z.

Calculate total energy and atomic forces.
 (*until iteration = 6 steps/atom x N atoms = 6N*)

12 iteration for graphene

4. Calculate force-constants and dynamical matrix (3Nx3N matrix). (6x6 matrix for graphene)

- 5. Obtain phonon dispersion and phonon density of states.
- 6. Write output files, i.e. \*.FORCE\_SETS, \*.PhDis, \*.PhDos



### **Phonon dispersion of diamond**



### Phonon density of states of diamond





8x8x8 supercell in real space

### Phonon density of states

$$I(\omega) = \frac{1}{n_k} \frac{1}{(2\pi)^3} \sum_{\alpha \in N} \sum_{\substack{i \in N \\ i \in N}} \sum_{\substack{i \in N \\ i \in N}} \frac{|A_i^{\alpha}(\omega)|^2}{|A_i^{\alpha}(\omega)|^2}$$
Number of k vectors
$$|A_i^{\alpha}(\omega)|^2 = A_{i,Re}^{\alpha}(\omega) \times A_{i,Re}^{\alpha}(\omega) - A_{i,Im}^{\alpha}(\omega) \times A_{i,Im}^{\alpha}(\omega)$$

where  $A(\omega)$  is the eigen-vector of atoms at a frequency  $\omega$ .



# **LO-TO splitting for polar system**



### Force-constants

$${}^{T}K_{I\alpha J\beta} = {an \atop i} K_{I\alpha J\beta} + {na \atop i} K_{I\alpha J\beta}$$
short-range interaction  
(analytic part) long-range interaction  
(non-analytic part) here is an extra polarization effect  
for the longitudinal optical phon  
due to the long-range nature of the  
Coulomb interaction. This polarization

X

Figure 1. Electrical macroscopic polarization P in a slab normal to z, for a vanishing external field  $\mathbf{E}^{(ext)}$ . Left: when **P** is normal to the slab, a depolarizing field  $\mathbf{E} = -4\pi \mathbf{P}$  is present inside the slab, and surface charges form, with areal density  $\sigma_{\text{surface}} = \mathbf{P} \cdot \mathbf{n}$ . Right: when **P** is parallel to the slab, no depolarizing field and no surface charge is present.

T

n effect phonon e of the arization effect results in an additional restoring force between the ions, yielding a higher longitudinal phonon frequency compared to the transverse optical phonon.

#### J. Phys.: Condens. Matter 22 (2010) 123201

### Analytic part and non-analytic part of force-constants

$${}^{T}K_{I\alpha J\beta} = {}^{an}K_{I\alpha J\beta} + {}^{na}K_{I\alpha J\beta}$$

analytic part

non-analytic part

where I and J are atomic index and  $\alpha$  and  $\beta$  are the direction of displacement.

#### BASIC LATTICE DYNAMICS OF POLAR SOLIDS

As phonons represent waves of collective atomic vibrations in a periodic pattern, we can choose to model a system by a repeated parallelepiped, i.e., a supercell. To formulate atomic vibrations within such a supercell, it is convenient to start from equations of motion for the atoms. For a polar solid, the forces can be divided into two additive contributions—analytic and nonanalytic.<sup>20</sup> The terms analytic and nonanalytic can be traced back to the mathematical definition<sup>41</sup> that a function is called analytic if and only if its Taylor series expansion about a reference point converges to the function at each point in some neighbourhood of the reference point, otherwise it is nonanalytic. Under the framework of first-principles calculations, the analytic contribution accounts for all the forces under the restricted periodic boundary conditions under which the averaged electric field is assumed to be zero. The nonanalytic contribution accounts the additional forces owing to a nonzero-averaged electric field.

### The general quadratic expression of energy



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Associated with electric polatization, there will be a macroscopic electric field E and an electric displacement D, related by equation (6).

electric polarization  

$$D = E + 4\pi P$$
(6)  
electrical induction  
/ electric displacement  

$$D - E = 4\pi P$$
(7)  

$$P = \frac{D - E}{4\pi}$$
(8)

In the absence of free external charges, the Maxwell equations give

In a longitudinal optical mode, the electric polarization P is parallel to q vector.

D<sub>LO</sub> must vanish.

$$\boldsymbol{D} = \boldsymbol{0} = \boldsymbol{E}_{LO} + 4\pi \boldsymbol{P}$$
(13)  
$$\boldsymbol{P} = -\frac{\boldsymbol{E}_{LO}}{4\pi}$$
(14)

In the absence of free external charges, the Maxwell equations give

 $E_{TO}$  must vanish.

D, E, and P II q vector

or

Combined with eq. (5) and (8), we get eq. (20).

$$\boldsymbol{D} \equiv -\frac{4\pi}{\Omega} \frac{\partial T(\boldsymbol{u}, \boldsymbol{E})}{\partial \boldsymbol{E}} = \frac{4\pi}{\Omega} \boldsymbol{u} \boldsymbol{e} \boldsymbol{Z} + \boldsymbol{\epsilon}_{\infty} \boldsymbol{E} \qquad (5)$$
$$\boldsymbol{P} = \frac{\boldsymbol{D} - \boldsymbol{E}}{4\pi} \qquad (8)$$

$$\boldsymbol{P} = \frac{\boldsymbol{D}}{4\pi} - \frac{\boldsymbol{E}}{4\pi} = \frac{\boldsymbol{u}\boldsymbol{e}\boldsymbol{Z}}{\Omega} + \frac{\boldsymbol{\epsilon}_{\infty}\boldsymbol{E}_{LO}}{4\pi} - \frac{\boldsymbol{E}_{LO}}{4\pi} \qquad (20)$$

After substituting eq. (14) into eq. (21), we can obtain eq. (22).

$$P = \frac{ueZ}{\Omega} + \frac{\epsilon_{\infty}E_{LO}}{4\pi} - \frac{E_{LO}}{4\pi}$$

$$P = -\frac{E_{LO}}{4\pi} = \frac{ueZ}{\Omega} + \frac{\epsilon_{\infty}E_{LO}}{4\pi} - \frac{E_{LO}}{4\pi}$$

$$0 = \frac{ueZ}{\Omega} + \frac{\epsilon_{\infty}E_{LO}}{4\pi}$$

$$E_{LO} = -\frac{4\pi}{\Omega}\frac{ueZ}{\epsilon_{\infty}}$$

$$E_{LO} + \frac{4\pi}{\Omega}\frac{u_{I}e\sum_{\nu}Z_{I}^{\nu\beta}\cdot\hat{q}_{\nu}}{\epsilon_{\infty}}$$

Ω

 $\epsilon_{\infty}$ 

(22)

(21)

### **Force-constants**

$$\frac{\partial T(u, \mathbf{E})}{\partial u_{I} \partial u_{J}} = \frac{\partial^{2} \left( \frac{1}{2} m \omega^{2} u^{2} - \frac{\Omega}{8\pi} \epsilon_{\infty} \mathbf{E}^{2} - \mathbf{M} \cdot \mathbf{E} \right)}{\partial u_{I} \partial u_{J}}$$
(23)  
$$^{T} K_{I\alpha J\beta} = \frac{\partial T(u, \mathbf{E})}{\partial u_{I} \partial u_{J}} = an K_{I\alpha J\beta} + na K_{I\alpha J\beta}$$
(24)  
$$an K_{I\alpha J\beta} = \frac{\partial^{2} \left( \frac{1}{2} m \omega^{2} u^{2} \right)}{\partial u_{I} \partial u_{J}}$$
(25)

analytic part of force constants

$${}^{na}K_{I\alpha J\beta} = \frac{\partial^2 \left(-\frac{\Omega}{8\pi}\epsilon_{\infty}E^2 - M \cdot E\right)}{\partial u_I \partial u_J}$$

$${}^{na}K_{I\alpha J\beta} = \frac{\partial^2(-\boldsymbol{M}\cdot\boldsymbol{E})}{\partial u_I\partial u_J}$$
(27)

(26)

$${}^{na}K_{I\alpha J\beta} = \frac{\partial^2 \left( \left( -u_I e \sum_{\gamma} Z_I^{\gamma \alpha} \right) \cdot \left( -\frac{4\pi}{\Omega} \frac{u_J e \sum_{\nu} Z_J^{\nu \beta}}{\epsilon_{\infty}} \right) \right)}{\partial u_I \partial u_J}$$
(28)

$$na_{K_{I\alpha J\beta}} = \frac{4\pi}{\Omega} \frac{e^2 (\sum_{\gamma} Z_I^{\gamma \alpha} \cdot \hat{q}_{\gamma}) \cdot (\sum_{\nu} Z_J^{\nu \beta} \cdot \hat{q}_{\nu})}{\sum_{\gamma} \sum_{\nu} \hat{q}_{\gamma} \cdot \epsilon_{\infty} \cdot \hat{q}_{\nu}}$$
(29)

### Born effective charge

Since the Born effective charge  $Z^*_{\alpha\beta}$  is defined by a tensor:

$$Z^*_{lphaeta} = rac{V_c}{|e|} rac{\Delta P_lpha}{\Delta u_eta}$$

where  $V_c$  is the volume of the unit cell, e the elementary charge,  $\Delta u_{\beta}$  displacement along  $\beta$ -coordinate,  $\Delta P_{\alpha}$  the change of macroscopic polarization along  $\alpha$ -coordinate, therefore we will perform the above procedures (1) and (2) at least two or three times by varying the x, y, or z-coordinate of Na atom. Then, for example, we have along x-coordinates

```
Px = 94.39497736 (Debye/unit cell) at x= -0.05 (Ang)
Px = 94.64718658 (Debye/unit cell) at x= 0.0 (Ang)
Px = 94.89939513 (Debye/unit cell) at x= 0.05 (Ang)
```

Thus,

$$Z_{xx}^* = \frac{(94.89939513 - 94.39497736)/(2.54174776)}{0.1/0.529177}$$
  
= 1.050

Codes:

polB.f read\_scfout.f read\_scfout.h

### Born effective charge tensors

$$Z^*_{\alpha\beta} = \frac{V_c}{|e|} \frac{\Delta P_\alpha}{\Delta u_\beta}$$

#### For example: SiC (primitive cell)

Setup input file and commands

2. Do the displacement from the 1<sup>st</sup> atom to last atom

3. Calculate total energy (and print sic.scfout file)

- CALL polB() to calculate electric polarization (P<sub>ii</sub>)
- Save P<sub>ii</sub> and come back to step 2 (*until iteration = 12*)
- Calculate Born effective charge tensors at each atom
- Apply acoustic sum rule and write sic.bec and sic.bect files.

Acoustic sum rule:

$$\sum_{k} Z_{k,\alpha\beta}^* = 0$$

Table 1. Each element of Born effective charge tensor of SiC are listed.

Si <sub>ij</sub>	x	У	z
x	2.693	0.000	0.000
у	0.000	2.693	0.000
z	0.000	0.000	2.693

Born effective charge of SiC : 2.697 from Raman scattering data.

C. Z. Wang, R. Yu, H. Krakauer, Phys. Rev. B, vol. 53, number 9, 5430-5437 (1996).

### Keywords for Born effective charge tensors

#### MD.Type BEC

When MD.Type is specified to be BEC, the atomic Born effective charge tensors will be calculated. In BEC calculation, the number of steps are number of atoms within primitive cell times 6. For example, in the Silicon Carbide case, there are 2 atoms within primitive cell, total number of steps for displacements are 12 steps (i.e. 2 atoms X 6 steps/atom).

#### PolB.fileout

If you want to calculate macroscopic electric polarizations of a bulk system based on the Berry phase formalism and output to files (\*.PhDos), then set the keyword 'PolB.fileout' to 'on'.

#### PolB.ReciVectors.NumGrids

Specify the number of grids to discretize reciprocal a-, b-, and c-vectors. For example,

PolB.ReciVectors.NumGrids 15 15 15 #default = 9 9 9

#### PolB.Direction

Specify the direction of polarization as reciprocal a-, b-, and c-vectors. For example,

 PolB.Direction 1 1 1
 #default = 1 1 1

 MD.Type
 BEC

 MD.FC.Displacement
 0.05
 # default=0.05

 PolB.fileout on
 # default = off / 0

 PolB.ReciVectors.NumGrids 9 9 9
 # default = 9 9 9

 PolB.Direction 1 1 1
 # default = 1 1 1

### Plot phonon dispersion - (1)

(1) We can use gcc to compile the 'FCFileReader\_161023.c' to generate an executable file (such as 'FCFileReader').

gcc FCFileReader\_161023.c -o FCFileReader -I /usr/include/x86\_64-linux-gnu/sys/ -L /home/ytl/LAPACK/lapack-3.5.0 -llapack -lrefblas -lgfortran -lm

(2) After 'FCFileReader' is created, we can perform this executable file to generate phonon dispersion file (\*.PhDis).

#### ./FCFileReader

Then, we have to input some data to perform phonon dispersion, acoustic sum rules, LO-TO splitting, and phonon density of states.

> Input name of \*.dat file : SiC\_7x7x7.dat Input name of \*.fc file : sic\_7x7x7.FORCE\_SETS Does it calculate LO-TO splitting? (Yes=0/No=1) 0 Input name of \*.bect file : sic.bect Does it need to apply acoustic sum rules? (Yes=0/No=1) 0 Input name of output file : sic\_7x7x7.PhDis Input a filename of phonon density of states : sic\_7x7x7.PhDos

### Plot phonon dispersion - (2)

It will generate sic\_7x7x7.PhDis (i.e. phonon dispersion data) and sic\_7x7x7.PhDos (i.e. phonon density of states data) in the directory.

(3) There is a file 'phondisp\_gnu16.c' in the 'FCReader' directory. Compile the file as follows:

gcc phondisp\_gnu16.c -Im -o phondisp\_gnu16

After the compile is completed correctly, one 'phondisp\_gnu16' executable file can be found in the same directory. Then, we run this executable file to generate both files, sic\_7x7x7.PhonDispDat1 and sic\_7x7x7.GNTPhonDisp, in the directory.

./phondisp\_gnu16 sic\_7x7x7.PhonDisp

```
Then, we input a number from 1 to 5 to select the unit we need. For example,
ytl@ytl-ubuntu14:~/Code_C_160607/IO$ ./phondisp_gnu16 sic_7x7x7.PhonDisp
Select the unit of frequency? (1) 1/cm, (2) THz, (3) eV, (4) meV, (5) mRyd. 1
sic_7x7x7.GNUPhonDisp is made
ytl@ytl-ubuntu14:~/Code_C_160607/IO$
```

(4) Finally, we use gnuplot to plot phonon dispersion, e.g. sic\_7x7x7.GNUPhonDisp. For example, we type in " gnuplot sic\_7x7x7.GNUPhonDisp ". The result is shown in Figure 3.

### Phonon dispersion of GaAs crystal (1)



### Phonon dispersion of GaAs crystal (2)

#### CASTEP

- 1. number of atoms in unit cell = 8.
- 2. supercell = 2x2x2
- 3. LDA
- 4. DIRECT method



M. Sternik et al. / Computational Materials Science 13 (1999) 232–238
J. Phys.: Condens. Matter 2 (1990) 1457–1474.



Fig. 1. Phonon dispersions calculated for GaAs and AlAs crystals. Experimental data (dottes) are taken from Refs. [2,3].

### Phonon dispersion of GaAs crystal (3)



M. Sternik et al. / Computational Materials Science 13 (1999) 232-238

Fig. 1. Phonon dispersions calculated for GaAs and AlAs crystals. Experimental data (dottes) are taken from Refs. [2,3].

### Phonon dispersion of SiC 7x7x7 supercell



### Phonon dispersion of SiC 7x7x7 supercell



# **Keywords for phonon dispersion**

### The format of input file (\*.dat) - (1)

### Graphene 9x9x1 supercell

(1) In order to perform the force-constants calculation, we write the keywords in the input file as below:

MD. Type	FC	
MD.FC.Displacement	0.05	# default value is 0.05 angstrom
MD.FC.Supercell.grid	991	# default value is 3 3 3

```
Atoms, Number 2
Atoms.SpeciesAndCoordinates.Unit Ang # Ang AU
<Atoms.SpeciesAndCoordinates # Unit=Ang.</pre>
1
  C
     1.23002520000
                     0.71014850000
                                         7.5000000000 2.00 2.00
2 C
       2.46007480000
                        1.42031150000
                                         7.5000000000 2.00 2.00
Atoms.SpeciesAndCoordinates>
Atoms.UnitVectors.Unit Ang # Ang AU
<Atoms.UnitVectors # unit=Ang.</pre>
   2.4600000000
                  0.0000000000
                                  0.0000000000
   1.2300000000 2.1303600000
                                  0.0000000000
   0.000000000
                  0.0000000000
                                 15.0000000000
Atoms.UnitVectors>
```

### The format of input file (\*.dat) - (2)

(2) And, the paths of the first Brillouin zone for constructing phonon dispersion of graphene are required. In this graphene case, we select 3 paths within the first Brillouin zone of graphene primitive cell (i.e. G->M, M->K, M->G). And, the option of applying acoustic sum rules into force-constants is turned on.

```
Phonon.Nkpath 3

<Phonon.kpath

173 0.000000 0.000000 0.000000 0.000000 0.500000 0.000000 G M

100 0.000000 0.500000 0.000000 0.333333 0.6666666 0.000000 M K

200 0.333333 0.6666666 0.000000 0.000000 0.000000 K G

Phonon.kpath>

PhonDisp.sumrule 0
```

(3) If the total phonon density of states and projected phonon density of states are required to calculate, the keywords will be listed as below.

```
PhDos.fileout on# switch on to calculate Phonon DOS.PhDos.FreRange -100.0 1700.0 1.0# initial Frequency, final frequency, delta frequencyPhDos.Kgrid 20 20 20PhDos.Kgrid 20 20 20
```

```
ProjectPhDos.Num.Atoms 1
<PhDos.SerialNumber.Atoms
1
PhDos.SerialNumber.Atoms>
```

### The format of input file (\*.dat) - (3)

(4) Therefore, we add these keywords into input file and then perform this force-constants calculation. In the end of calculation, the \*.FORCE\_SETS, \*.PhDis (for phonon dispersion), and \*.PhDos (for phonon density of states) files will be generated. We use "phondisp\_gnu16.c" code to generate a phonon dispersion file (i.e. \*.PhonDispDAT1) and a \*.GNUPhonDisp file for plot phonon dispersion by GNUPLOT. Then, we type in

#### ./phondisp\_gnu16 \*.GNUPLOT



Figure 1. The phonon dispersion of graphene 9x9x1 supercell with acoustic sum rules and corresponding phonon density of states are shown. In phonon density of states, the black line and the green line are total phonon density of states and projected phonon density of states, respectively.

### The format of forces (\*.FORCE SETS)

Example : Graphene 9x9x1 supercell ytl@ytl-4309: ~/Code\_C/IO # of atoms within a supercell 162 # of displaced atoms displacement along a direction (x,y,z) 2 81 the first index of displaced atom 0.05000000000000000 0.00000000000000000 0.00000000000000000 -0.000000000 atomic forces (x,y,z) with index 1 -0.00005094550.0000593526 -0.00002151780.000000000 atomic forces (x,y,z) with index 2 -0.00003724330.0001921197 0.0002289062 0.0000000000 -0.0002160127-0.00005681130.0000000000 -0.0000397708 0.0000330430 0.0000000000 1600 1400 1200 wavelength (1/cm) 1000 800 600 400 200 0 М K

G

Fig 1. The phonon dispersion of graphene 9x9x1 supercell

G

### Dielectric constant and Born effective charge tensors

#### Example : SiC crystal (File : sic.bect)

😣 🖨 🗊 yl	l@ytl-430	9: ~/Code_	c/10						
default v	alue								dielectric constant
6.520	0.000	0.000	0.000	6.520	0.000	0.000	0.000	6.520	from Experiment.
2.693	0.000	0.000	0.000	2.693	0.000	0.000	0.000	2.693	BEC tensor of Si atom
-2.693	0.000	0.000	0.000	-2.693	-0.000	0.000	-0.000	-2.693	BEC tonsor of C stom
XX	ху	XZ	ух	уу	УZ	ZX	ZY	ZZ	BEC lensor of C alom

Experimental value of Si atom is 2.697.

C. Z. Wang, R. Yu, H. Krakauer, Phys. Rev. B, vol. 53, number 9, 5430-5437 (1996).

# Implementation of phonon dispersion

### **Dynamical matrix**

```
for (i=0;i<noa3;i++){</pre>
  for (j=0;j<noa3;j++){</pre>
    double sumbre=0.0,sumbim=0.0;
    for (o=0;o<fl;o++){ // unit cell R'</pre>
       double uv[3][3],rlvt[3][3],pf;
       for (ii=0;ii<3;ii++)</pre>
         for (jj=0;jj<3;jj++){</pre>
            uv[ii][jj]=unitvectors ori[o][ii][jj]-unitvectors ori[aa2][ii][jj]; // R(p)-R(0)
            rlvt[jj][ii]=q[t][jj]*rlv[jj][ii]; // q[3] * reciprocal lattice vectors[3][3] = rlvt
         }
       pf=two lattices product(uv[0],uv[1],uv[2],rlvt[0],rlvt[1],rlvt[2]); // rlvt dot R(p)-R(0)
       sumbre+=fcmatrix[i][o*noa3+j]*cos(pf);
       sumbim+=fcmatrix[i][o*noa3+j]*sin(pf);
    double sqrt mimj=sqrt(atomic mass[i/3]*atomic mass[j/3]); // calculate 1/sqrt(mi*mj)
    Dre[i][j]=sumbre/sqrt mimi;
    Dim[i][j]=sumbim/sqrt mimj; // D[q][ix3][jx3]
                                    \widetilde{D}_{I\alpha J\beta}(\vec{q}) = \frac{1}{\sqrt{m_I m_J}} \sum_{\vec{p},\vec{p}'} K_{I\alpha J\beta}(\vec{R}' - \vec{R}) e^{i\vec{q}\cdot(\vec{R}' - \vec{R})}
```

Mass of J-th atom

### LO-TO splitting - (1)

#### if (isLOTOSplitting==0){

// ### Non-analytic term of force constant for polar crystals ###

```
// ### if q is very close to 0, non-analytic term can not be calculated ###
 // if ( |qx|+|qy|+|qz| ) is smaller than 0.000001
if (fabs(q[t][0])+fabs(q[t][1])+fabs(q[t][2]) <= 0.000001)
  q[t][0]=0.0000001;
  q[t][1]=0.0000001;
                                                                    \frac{4\pi}{\Omega} \frac{e^2 (\sum_{\gamma} Z_I^{\gamma \alpha} \cdot \hat{q}_{\gamma}) \cdot (\sum_{\nu} Z_I^{\nu \beta} \cdot \hat{q}_{\nu})}{\sum_{\nu} \sum_{\nu} \hat{q}_{\nu} \cdot \epsilon_{\infty} \cdot \hat{q}_{\nu}}
  q[t][2]=0.0000001;
// q vector
double qv[3]; // define unit vector a
// transform q[3] to Cartesian coordinates (x,y,z).
// It's axis will be the same as axis of Born effective charge tensor[3][3].
// i.e. ( q x reciprocal lattice constants ).
qv[0]=q[t][0]*rlv[0][0]+q[t][1]*rlv[0][1]+q[t][2]*rlv[0][2];
qv[1]=q[t][0]*rlv[1][0]+q[t][1]*rlv[1][1]+q[t][2]*rlv[1][2];
qv[2]=q[t][0]*rlv[2][0]+q[t][1]*rlv[2][1]+q[t][2]*rlv[2][2];
// calculate qv[1][3] X dielectric constant tensor [3][3] X qv [3][1]
double qvxdixqv=qv[0]*(di[0][0]*qv[0]+di[0][1]*qv[1]+di[0][2]*qv[2])
                 +qv[1]*(di[1][0]*qv[0]+di[1][1]*qv[1]+di[1][2]*qv[2])
                 +qv[2]*(di[2][0]*qv[0]+di[2][1]*qv[1]+di[2][2]*qv[2]);
// get volume, define e2, and calculate 4*PI*e2/V
double V=get volume(tv[0],tv[1],tv[2]);
double e2=1.0; // unit of electron
double pix4xe2dV=PI*4*e2/V;
```

### LO-TO splitting - (2)

// ### start to calculate non-analytic term of force constants ###
int atomi,atomi\_dir,atomj,atomj\_dir;
for (i=0;i<noa3;i++){
 atomi=i/3; // index of atom i
 atomi\_dir=i%3;
 // index of alpha direction of Born effective charge at atom i
 // i.e. 0=x, 1=y, 2=z</pre>

// first Z dot q
double zql=bect[atomi][atomi\_dir][0]\*qv[0]
 +bect[atomi][atomi\_dir][1]\*qv[1]
 +bect[atomi][atomi\_dir][2]\*qv[2];

$${}^{na}K_{I\alpha J\beta} = \frac{4\pi}{\Omega} \frac{e^2 \left( \sum_{\gamma} Z_I^{\gamma \alpha} \cdot \hat{q}_{\gamma} \right) \cdot \left( \sum_{\nu} Z_I^{\nu \beta} \cdot \hat{q}_{\nu} \right)}{\sum_{\gamma} \sum_{\nu} \hat{q}_{\gamma} \cdot \epsilon_{\infty} \cdot \hat{q}_{\nu}}$$

// calculate q\*Za x (4PI/V) / (q x dielectic constant x q)
double t1=zq1\*(pix4xe2dV/qvxdixqv);

```
for (atomj=0;atomj<number_of_atoms;atomj++){ // atomj = index of atom j
    for (atomj_dir=0;atomj_dir<3;atomj_dir++){</pre>
```

// index of beta direction of Born effective charge at atom j, // i.e. 0=x, 1=y, 2=z

#### fcmatrix[i][atomj\*3+atomj\_dir]+=zq2\*t1;

}

```
// = fcmatrix[i][j*3+k]+=zq1*zq2*(pix4xe2dV/qvxdixqv);
// calculate q*Za x Zb*q x (4*PI/V) / (q x dielectic constant x q)
```

### Acoustic sum rules

